

IRFU224 Information



For Reference Only

Part Number IRFU224

Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 250V 3.8A I-PAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRFU224 Specifications

Manufacturer Part Number IRFU224 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 3.8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 260PF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 42W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251AA Package / Case TO-251AS		
CategoryDiscrete Semiconductor ProductsFansistors - FETs, MOSFETs - SinglePackageTO-251-3 Short Leads, IPak, TO-251AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C3.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs14nC @ 10VInput Capacitance (Ciss) (Max) @ Vds260pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251AAPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Manufacturer Part Number	IRFU224
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C3.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs14nC @ 10VInput Capacitance (Ciss) (Max) @ Vds260pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251AAPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Series	-
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.3A, 10V Operating Temperature Supplier Device Package Package / Case 3.8A (Tc) 4V @ 250µA 4V @ 250µA 260pF @ 25V 25V 70-251AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs14nC @ 10VInput Capacitance (Ciss) (Max) @ Vds260pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251AAPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	250V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Founding Type Through Hole Supplier Device Package TO-251-3 Short Leads, IPak, TO-251AA	Current - Continuous Drain (Id) @ 25°C	3.8A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251AA Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251AA Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-251AAPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	14nC @ 10V
FET Feature - Power Dissipation (Max) 2.5W (Ta), 42W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251AA Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	260pF @ 25V
Power Dissipation (Max) 2.5W (Ta), 42W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251AA Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251AA Package / Case TO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-251AA Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	2.5W (Ta), 42W (Tc)
Mounting Type Through Hole Supplier Device Package TO-251AA Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	1.1 Ohm @ 2.3A, 10V
Supplier Device Package TO-251AA Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	TO-251AA
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

IRFU224 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFU224 Payment Methods





















IRFU224 Shipping Methods













If you have any question about IRFU224, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com